FAIRCHILD

SEMICONDUCTOR®

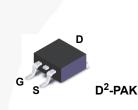
IRFW630B N-Channel MOSFET 200 V, 9 A, 400 mΩ

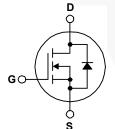
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supply and motor control.

Features

- 9.0 A, 200 V, $R_{DS(on)}$ = 400 m Ω (Max.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 22 nC)
- Low C_{rss} (Typ. 22 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter	IRFW630BTM_FP001	Unit
V _{DSS}	Drain-Source Voltage	200	V
ID	Drain Current - Continuous (T _C = 25°C)	9.0	А
	- Continuous (T _C = 100°C)	5.7	А
I _{DM}	Drain Current - Pulsed (Note 1)	36	A
V _{GSS}	Gate-Source voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	160	mJ
I _{AR}	Avalanche Current (Note 1)	9.0	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)	7.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^*$	3.13	W
	Power Dissipation $(T_C = 25^{\circ}C)$	72	W
	- Derate above 25°C	0.57	W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
Τ _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

Thermal Characteristics

Symbol	Parameter	IRFW630BTM_FP001	Unit	
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	1.74		
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient (Min. Pad of 2-oz Copper), Max.	62.5	°C/W	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40		

Device Marking Device		Package Reel Size		T	ape Widtl	n Qu	uantity	
IRFW630B IRFW630BTM_FP001		D ² -PAK	330 mm		24 mm	80	0 units	
Electric	al Cha	racteristics T _c =25°C un	less otherwise noted.					
Symbol		Parameter	Condi	tions	Min	Тур	Max	Unit
Off Charac	teristics							
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = 250 μA		200			V
ΔΒV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu$ A, Referenced to 25°C			0.2		V/ºC
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} = 200 V, V _{GS}	= 0 V			10	μA
			V _{DS} = 160 V, T _C = 125°C				100	μA
I _{GSSF}	Gate-Boo	ly Leakage Current, Forward	V _{GS} = 30 V, V _{DS} =	= 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse		V _{GS} = -30 V, V _{DS} = 0 V				-100	nA
On Charac	teristics							
V _{GS(th)}	Gate Threshold Voltage		$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} = 10 V, I _D = 4.5 A			0.34	0.4	Ω
9 _{FS}	Forward Transconductance		V _{DS} = 40 V, I _D = 4.5 A			7.05		S
Dynamic C	haracteris	stics						
C _{iss}	Input Cap	pacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		-	550	720	pF
C _{oss}	Output C	apacitance				85	110	pF
C _{rss}	Reverse	Transfer Capacitance				22	29	pF
Switching	Character	istics						
t _{d(on)}	Turn-On Delay Time		V _{DD} = 100 V, I _D = 9.0 A		11	30	ns	
t _r	Turn-On	Rise Time	R _G = 25 Ω			70	150	ns
t _{d(off)}	Turn-Off	Delay Time				60	130	ns
t _f	Turn-Off	Fall Time		(Note 4)		65	140	ns
Qg	Total Gat	e Charge	V _{DS} = 160 V, I _D =	9.0 A		22	29	nC
Q _{gs}	Gate-Sou	Irce Charge	V _{GS} = 10 V (Note 4)			3.6		nC
Q _{gd}	Gate-Dra	in Charge				10.2		nC
Drain-Sou	rce Diode	Characteristics and Maximu	m Ratings		-/			
I _S	Maximum Continuous Drain-Source Did		ode Forward Current				9.0	А
I _{SM}	Maximum Pulsed Drain-Source Diode I		Forward Current				36	Α
V _{SD}	Drain-So	urce Diode Forward Voltage	V _{GS} = 0 V, I _S = 9.0				1.5	V
t _{rr}	Reverse	Recovery Time	$V_{GS} = 0 V, I_{S} = 9.0$	A C		140		ns
Q _{rr}	Reverse	Recovery Charge	dl _F /dt =100 A/μs			0.87		μC

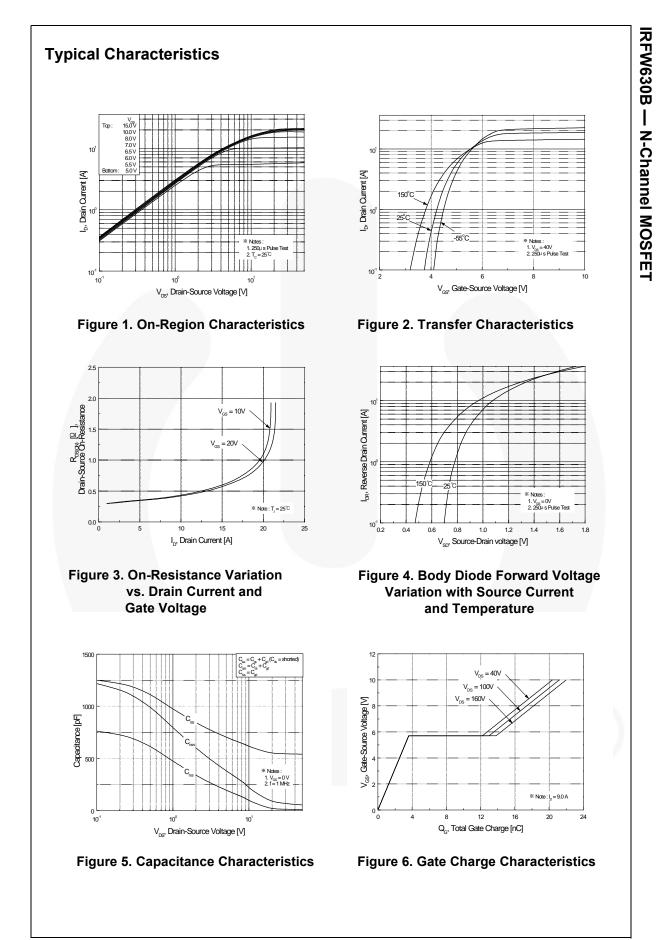
Notes:

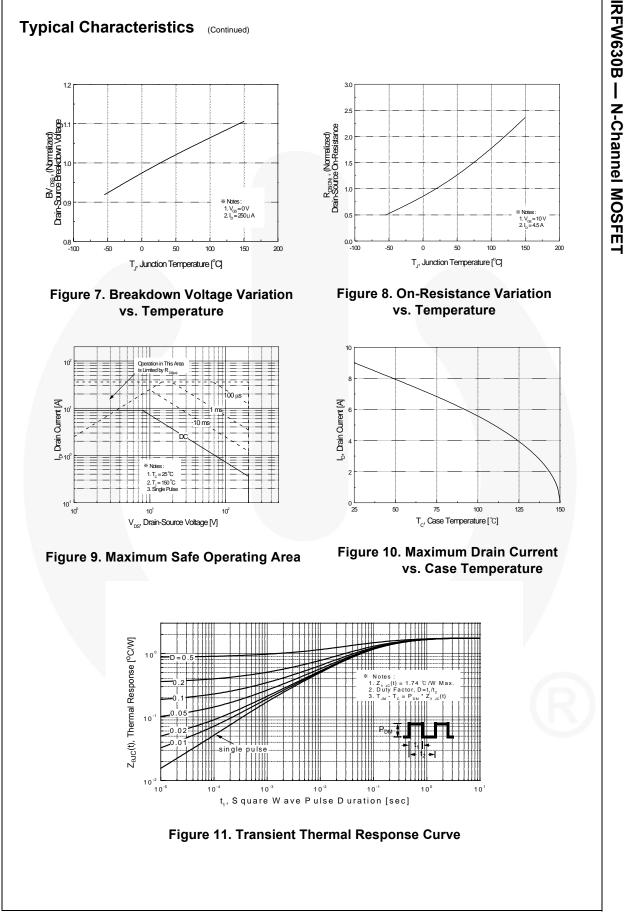
1. Repetitive rating: pulse-width limited by maximum junction temperature.

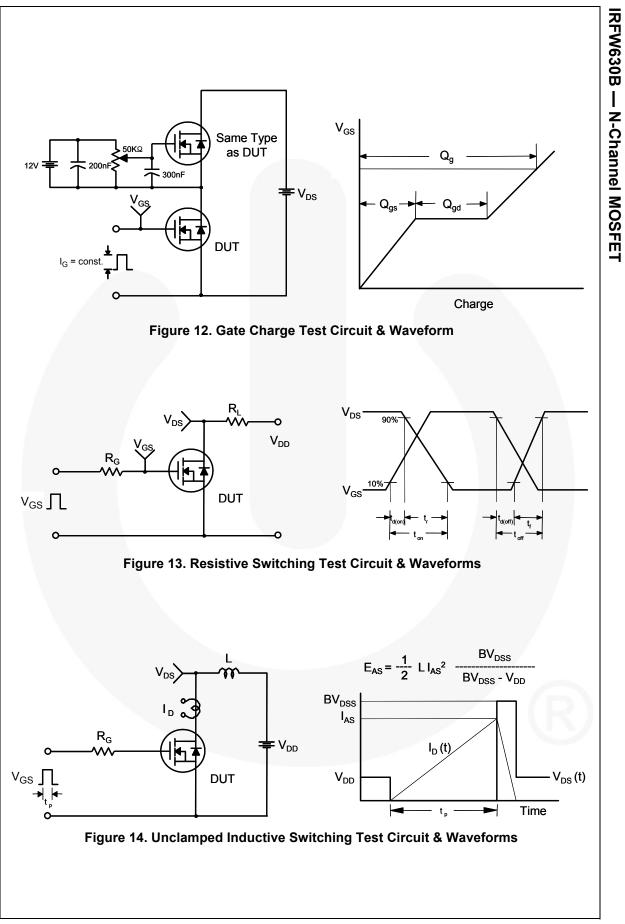
2. L = 3 mH, I_{AS} = 9.0 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

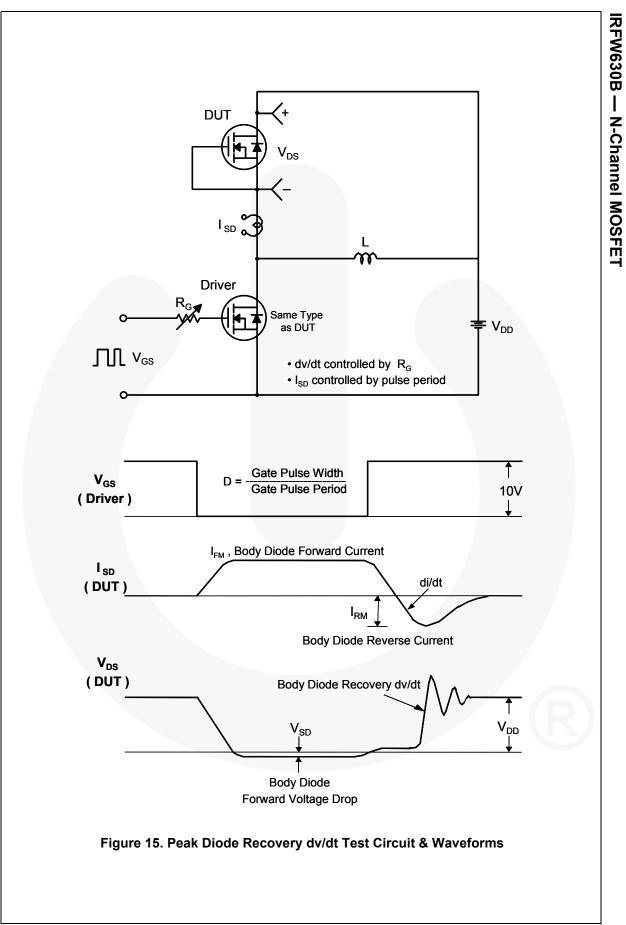
3. I_{SD} \leq 9.0 A, di/dt \leq 300 A/µs, V_{DD} \leq BV_{DSS,} starting ~T_J = 25°C.

4. Essentially independent of operating temperature.











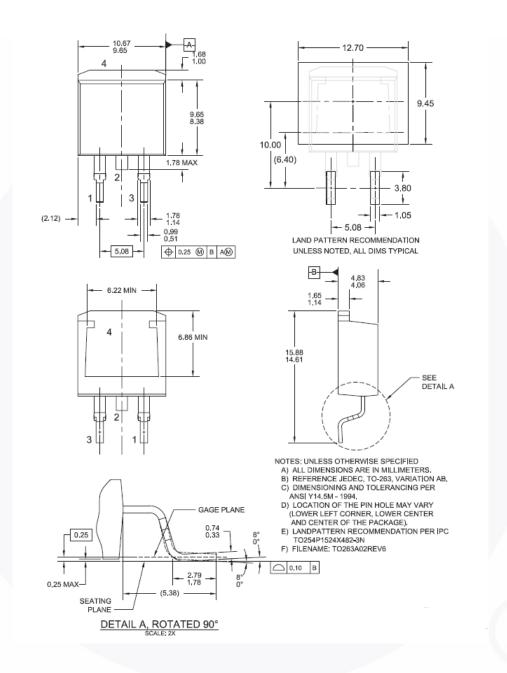


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower TM AX-CAP [®] * BitSIC TM Build it Now TM CorePLUS TM CorePOWER TM <i>CROSSVOLT</i> TM CTL TM CUrrent Transfer Logic TM DEUXPEED [®] Dual Cool TM EcoSPARK [®] EfficentMax TM ESBC TM Facre [®] Fairchild [®] Fairchild [®] Fairchild [®] Fairchild [®] Fairchild [®] Facre Could Series TM FACT FACT [®] FastvCore TM FETBench TM FPS TM	F-PFS [™] FRFET [®] Global Power Resource SM Green FPS [™] Green FPS [™] e-Series [™] Gmax [™] GTO [™] IntelliMAX [™] ISOPLANAR [™] Marking Small Speakers Sound Lor and Better [™] MegaBuck [™] MicroPLANAR [™] MicroPak2 [™] MotionMax [™] mWSaver [®] OptoHiT [™] OPTOLOGIC [®] OPTOPLANAR [®]	PowerXS™ Programmable Active Droop™ QFET® QS™ Quiet Series™ RapidConfigure™ Wor Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ Solutions for Your Success™ SPM® STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SuperMOS® SyncFET™	Sync-Lock TM System \mathbb{S}^* GENERAL TinyBoost [®] TinyDuck [®] TinyCalc TM TinyLogic [®] TINYOPTO TM TinyPOWer TM TinyPOWer TM TinyPWM TM TinyPWTM TinyPOWer TM TriFault Detect TM TriFault Detect TM TRECURRENT [®] * μ SerDes TM UHC [®] UHC
--	--	--	---

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3